TOSHIBA

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

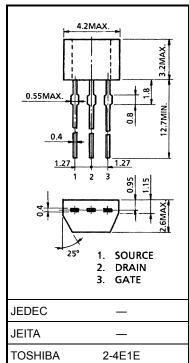
2SK1061

High Speed Switching Applications Analog Switch Applications Interface Applications

- Excellent switching times: $t_{on} = 14 \text{ ns}$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ mS} \text{ (min)}$
- Low on resistance: R_{DS} (ON) = 0.6 Ω (typ.)
- Enhancement-mode
- Complementary to 2SJ167

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC	ID	200	mA	
	Pulse	I _{DP}	800		
Drain power dissipation (Ta = $25^{\circ}C$)		PD	300	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Weight: 0.13 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

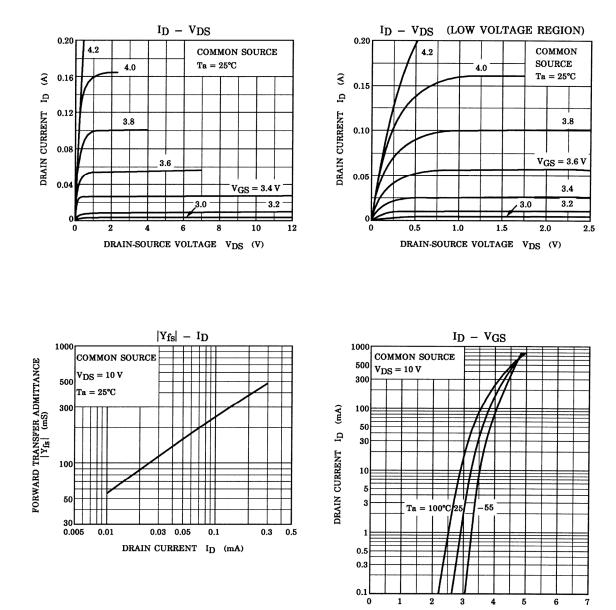
Unit: mm

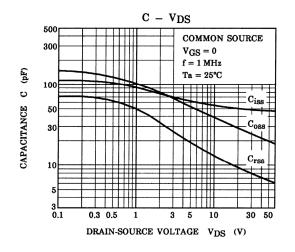
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 10~V,~V_{DS}=0$	_		±100	nA
Drain cut-off current		I _{DSS}	$V_{DS} = 60 V, V_{GS} = 0$			10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 1 \text{ mA}, V_{GS} = 0$	60		_	V
Gate threshold voltage		V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2		3.5	V
Forward transfer admittance		Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ mA}$	100		_	mS
Drain-source ON	resistance	R _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		0.6	1.0	Ω
Drain-source ON voltage		V _{DS (ON)}	$I_D = 50 \text{ mA}, V_{GS} = 10 \text{ V}$		30	50	mV
Input capacitance		C _{iss}			55	65	pF
Reverse transfer capacitance		C _{rss}	$V_{DS}=10~V,~V_{GS}=0,~f=1~MHz$		13	18	pF
Output capacitance		C _{oss}			40	50	pF
Switching time	Rise time	tr	$10 \text{ V} \qquad I_{\text{D}} = 100 \text{ mA}$		8	_	- ns
	Turn-on time	t _{on}	$\begin{array}{c} 0 \downarrow \downarrow V \\ 10 \mu s_{0} \downarrow \downarrow \\ \vdots \\ \vdots$	_	14		
	Fall time	t _f	D.U. ≦ 1%		35	_	
	Turn-off Time	t _{off}	V_{IN} : t_r , $t_f < 5$ ns $(Z_{out} = 50 \ \Omega)$		75		

Note: This transistor is the electrostatic sensitive device. Please handle with caution.

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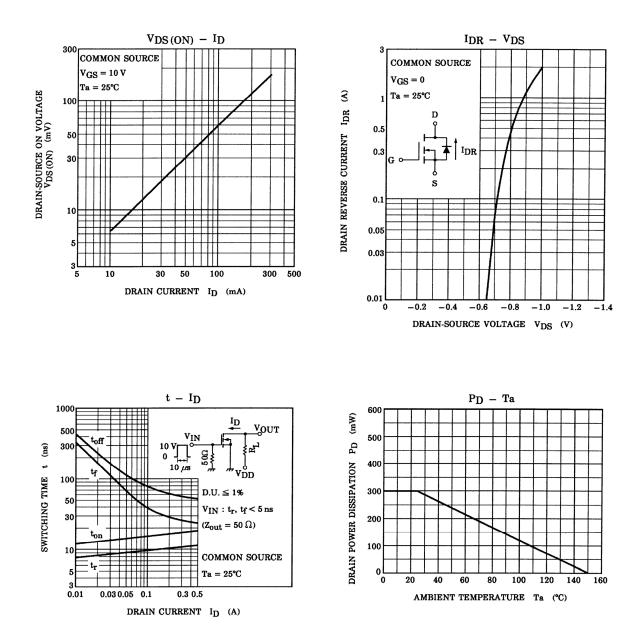


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3

GATE-SOURCE VOLTAGE V_{GS} (V)

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20070701-EN GENERAL

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